



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	30A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	21m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	26m
T_{jmax} (at $T_{case}=25^{\circ}C$)	100%



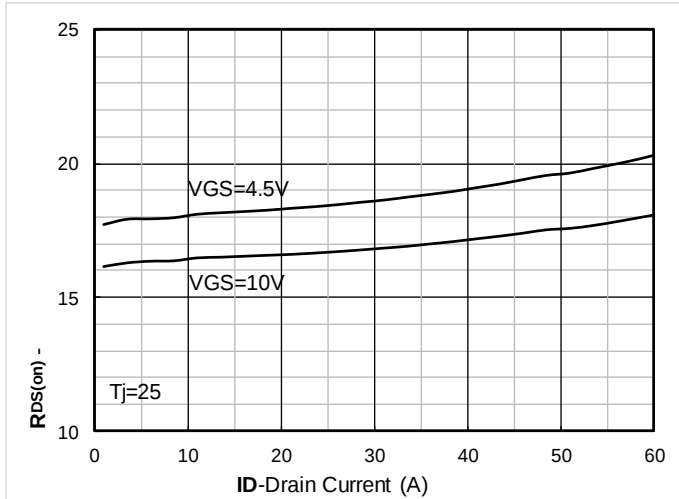


Figure 7. RDS(on) VS Drain Current

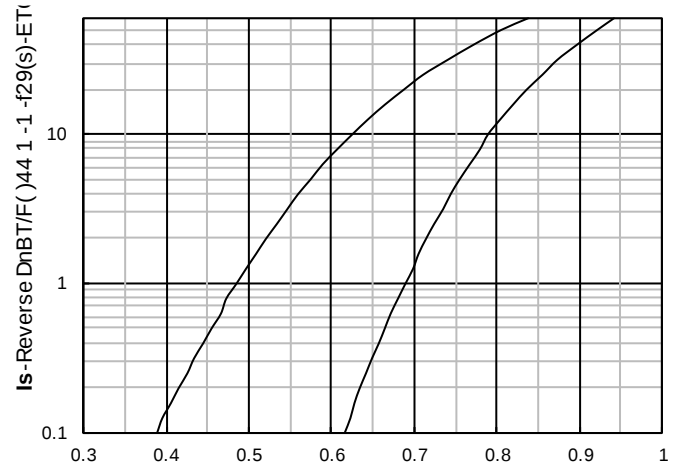


Figure 8. Forward characteristics of reverse diode

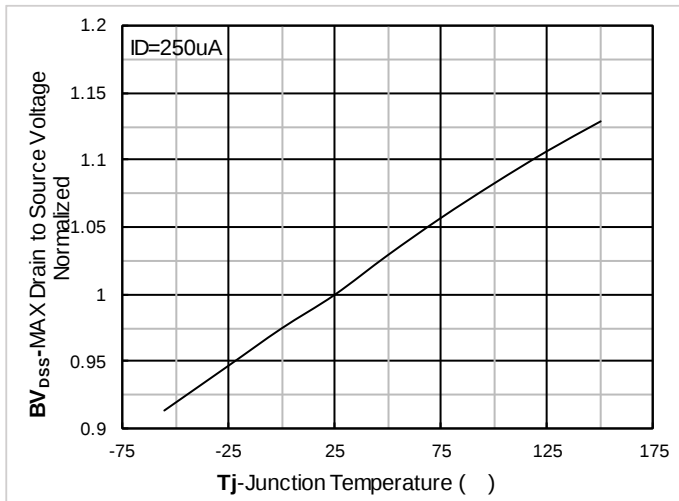


Figure 9. Normalized breakdown voltage

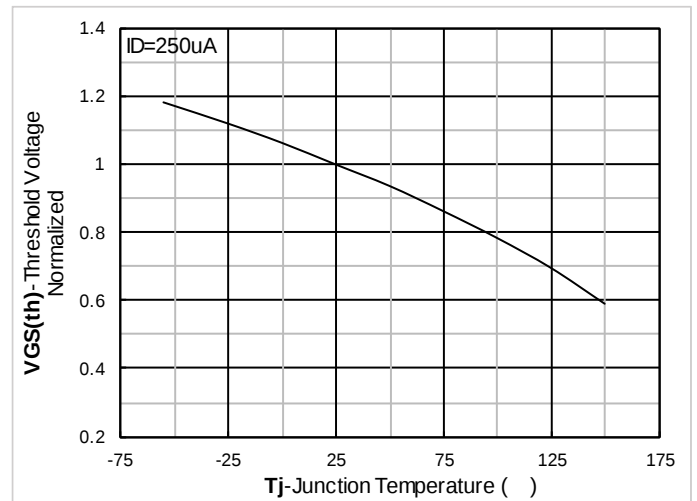


Figure 10. Normalized Threshold voltage

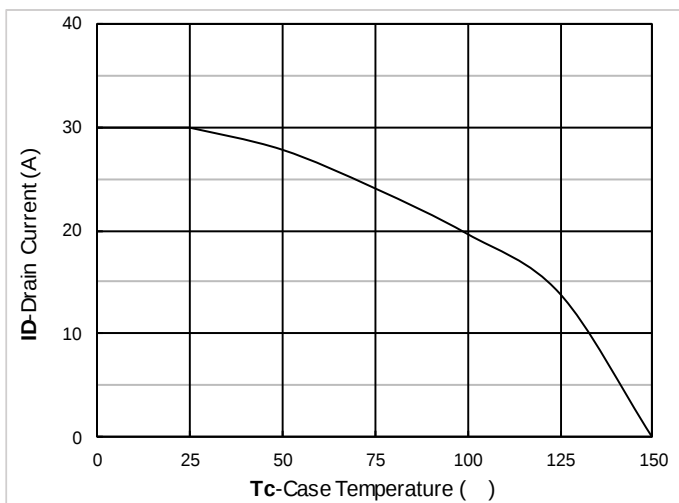


Figure 11. Current dissipation



Figure 12. Power dissipation



Figure 13. Maximum Transient Thermal Impedance

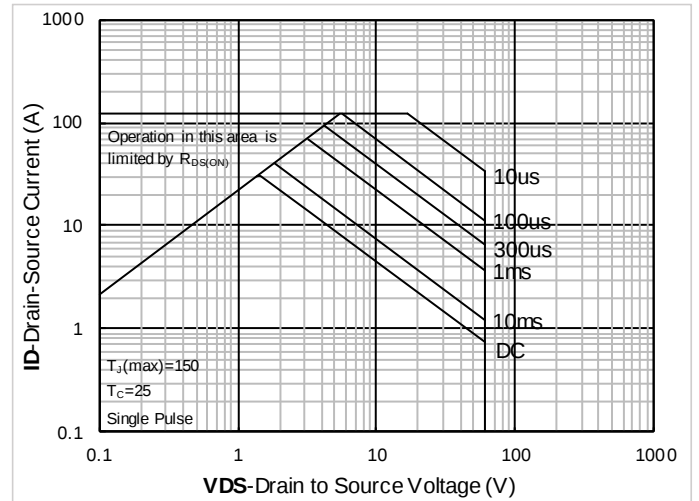


Figure 14. Safe Operation Area



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